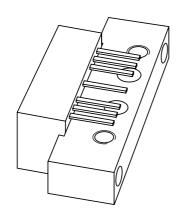
DISCRETE SEMICONDUCTORS

DATA SHEET



BGD704 750 MHz, 20 dB gain power doubler amplifier

Product specification Supersedes data of 2001 Oct 29 2001 Nov 02





Philips Semiconductors

750 MHz, 20 dB gain power doubler amplifier

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FEATURES

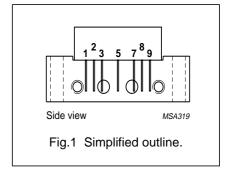
- Excellent linearity
- · Extremely low noise
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

APPLICATIONS

• CATV systems in the frequency range of 40 to 750 MHz.

PIN **DESCRIPTION** 1 input 2 common 3 common 5 $+V_B$ 7 common 8 common 9 output

PINNING - SOT115J



DESCRIPTION

Hybrid amplifier module operating at a voltage supply of 24 V (DC) encapsulated in a SOT115J package.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz	19.5	20.5	dB
		f = 750 MHz	20	_	dB
I _{tot}	total current consumption (DC)	V _B = 24 V	_	435	mA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER		MAX.	UNIT
V _i	RF input voltage	_	65	dBmV
T _{stg}	storage temperature	-40	+100	°C
T _{mb}	operating mounting base temperature	-20	+100	°C

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CHARACTERISTICS

Table 1 Bandwidth 40 to 750 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75$ Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Gp	power gain	f = 50 MHz	19.5	20	20.5	dB
		f = 750 MHz	20	21	_	dB
SL	slope cable equivalent	f = 40 to 750 MHz	0	1	2	dB
FL	flatness of frequency response	f = 40 to 750 MHz	_	±0.2	±0.5	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	31	_	dB
		f = 80 to 160 MHz	19	29	_	dB
		f = 160 to 320 MHz	18	25	_	dB
		f = 320 to 640 MHz	17	21	_	dB
		f = 640 to 750 MHz	16	21	_	dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	26	_	dB
		f = 80 to 160 MHz	19	27	_	dB
		f = 160 to 320 MHz	18	26	_	dB
		f = 320 to 640 MHz	17	24	_	dB
		f = 640 to 750 MHz	16	23	_	dB
S ₂₁	phase response	f = 50 MHz	-45	_	+45	deg
СТВ	composite triple beat	110 channels flat; V _o = 44 dBmV; measured at 745.25 MHz	_	-58	-57	dB
X _{mod}	cross modulation	110 channels flat; V _o = 44 dBmV; measured at 55.25 MHz	_	-63	-61	dB
CSO	composite second order distortion	110 channels flat; $V_0 = 44 \text{ dBmV}$; measured at 746.5 MHz	-	-61	-56	dB
d ₂	second order distortion	note 1	_	-75	-66	dB
Vo	output voltage	$d_{im} = -60 \text{ dB}$; note 2	60.5	63.5	_	dBmV
F	noise figure	f = 50 MHz	_	4.5	5	dB
		f = 450 MHz	_	_	6.5	dB
		f = 550 MHz	_	_	7	dB
		f = 600 MHz	_	_	7	dB
		f = 750 MHz	_	6.5	8.5	dB
I _{tot}	total current consumption (DC)	note 3	_	425	435	mA

Notes

- 1. $f_p = 55.25 \text{ MHz}$; $V_p = 44 \text{ dBmV}$; $f_q = 691.25 \text{ MHz}$; $V_q = 44 \text{ dBmV}$; measured at $f_p + f_q = 746.5 \text{ MHz}$.
- 2. Measured according to DIN45004B:

 $f_p = 740.25 \text{ MHz}; V_p = V_o;$

 $f_q = 747.25 \text{ MHz}; V_q = V_o - 6 \text{ dB};$

 $f_r = 749.25 \text{ MHz}; V_r = V_o - 6 \text{ dB};$

measured at $f_p + f_q - f_r = 738.25$ MHz.

3. The module normally operates at V_B = 24 V, but is able to withstand supply transients up to 30 V.

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Table 2 Bandwidth 40 to 600 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75$ Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Gp	power gain	f = 50 MHz	19.5	20	20.5	dB
		f = 600 MHz	20	20.7	_	dB
SL	slope cable equivalent	f = 40 to 600 MHz	0	_	2	dB
FL	flatness of frequency response	f = 40 to 600 MHz	_	_	±0.3	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	31	_	dB
		f = 80 to 160 MHz	19	29	_	dB
		f = 160 to 320 MHz	18	25	_	dB
		f = 320 to 600 MHz	17	21	_	dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	26	_	dB
		f = 80 to 160 MHz	19	27	_	dB
		f = 160 to 320 MHz	18	26	_	dB
		f = 320 to 600 MHz	17	24	_	dB
S ₂₁	phase response	f = 50 MHz	-45	_	+45	deg
СТВ	composite triple beat	85 channels flat; V ₀ = 44 dBmV; measured at 595.25 MHz	_	-65	-64	dB
X _{mod}	cross modulation	85 channels flat; V _o = 44 dBmV; measured at 55.25 MHz	_	-65	-64	dB
CSO	composite second order distortion	85 channels flat; V _o = 44 dBmV; measured at 596.5 MHz	_	-66	-58	dB
d ₂	second order distortion	note 1	_	_	-68	dB
Vo	output voltage	$d_{im} = -60 \text{ dB}$; note 2	63	_	_	dBmV
F	noise figure	see Table 1	_	_	_	dB
I _{tot}	total current consumption (DC)	note 3	_	425	435	mA

Notes

```
1. f_p = 55.25 MHz; V_p = 44 dBmV; f_q = 541.25 MHz; V_q = 44 dBmV; measured at f_p + f_q = 596.5 MHz.
```

2. Measured according to DIN45004B:

```
\begin{split} f_p &= 590.25 \text{ MHz; } V_p = V_o; \\ f_q &= 597.25 \text{ MHz; } V_q = V_o - 6 \text{ dB;} \\ f_r &= 599.25 \text{ MHz; } V_r = V_o - 6 \text{ dB;} \\ \text{measured at } f_p + f_q - f_r = 588.25 \text{ MHz.} \end{split}
```

3. The module normally operates at $V_B = 24 \text{ V}$, but is able to withstand supply transients up to 30 V.

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Table 3 Bandwidth 40 to 550 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75$ Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Gp	power gain	f = 50 MHz	19.5	20	20.5	dB
·		f = 550 MHz	20	20.6	_	dB
SL	slope cable equivalent	f = 40 to 550 MHz	0	_	2	dB
FL	flatness of frequency response	f = 40 to 550 MHz	_	_	±0.3	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	31	_	dB
		f = 80 to 160 MHz	19	29	_	dB
		f = 160 to 320 MHz	18	25	_	dB
		f = 320 to 550 MHz	17	21	_	dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	26	_	dB
		f = 80 to 160 MHz	19	27	_	dB
		f = 160 to 320 MHz	18	26	_	dB
		f = 320 to 550 MHz	17	24	_	dB
S ₂₁	phase response	f = 50 MHz	-45	_	+45	deg
СТВ	composite triple beat	77 channels flat; $V_0 = 44 \text{ dBmV}$; measured at 547.25 MHz	_	-67	-66	dB
X _{mod}	cross modulation	77 channels flat; V _o = 44 dBmV; measured at 55.25 MHz	_	-67	-66	dB
CSO	composite second order distortion	77 channels flat; V _o = 44 dBmV; measured at 548.5 MHz	_	-67	-60	dB
d ₂	second order distortion	note 1	_	_	-70	dB
Vo	output voltage	d _{im} = -60 dB; note 2	63.5	_	_	dBmV
F	noise figure	see Table 1	_	_	_	dB
I _{tot}	total current consumption (DC)	note 3	_	425	435	mA

Notes

```
1. f_p = 55.25 MHz; V_p = 44 dBmV; f_q = 493.25 MHz; V_q = 44 dBmV; measured at f_p + f_q = 548.5 MHz.
```

2. Measured according to DIN45004B:

```
\begin{split} f_p &= 540.25 \text{ MHz; } V_p = V_o; \\ f_q &= 547.25 \text{ MHz; } V_q = V_o - 6 \text{ dB;} \\ f_r &= 549.25 \text{ MHz; } V_r = V_o - 6 \text{ dB;} \\ \text{measured at } f_p + f_q - f_r = 538.25 \text{ MHz.} \end{split}
```

3. The module normally operates at $V_B = 24 \text{ V}$, but is able to withstand supply transients up to 30 V.

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Table 4 Bandwidth 40 to 450 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75$ Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Gp	power gain	f = 50 MHz	19.5	20	20.5	dB
·		f = 450 MHz	20	20.6	_	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0	_	2	dB
FL	flatness of frequency response	f = 40 to 450 MHz	_	_	±0.3	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	31	_	dB
		f = 80 to 160 MHz	19	29	_	dB
		f = 160 to 320 MHz	18	25	_	dB
		f = 320 to 450 MHz	17	21	_	dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	26	_	dB
		f = 80 to 160 MHz	19	27	_	dB
		f = 160 to 320 MHz	18	26	_	dB
		f = 320 to 450 MHz	17	25	_	dB
S ₂₁	phase response	f = 50 MHz	-45	_	+45	deg
СТВ	composite triple beat	60 channels flat; V ₀ = 46 dBmV; measured at 445.25 MHz	_	_	-67	dB
X _{mod}	cross modulation	60 channels flat; V _o = 46 dBmV; measured at 55.25 MHz	_	_	-64	dB
CSO	composite second order distortion	60 channels flat; V _o = 46 dBmV measured at 446.5 MHz	_	_	-63	dB
d ₂	second order distortion	note 1	_	_	-73	dB
Vo	output voltage	d _{im} = -60 dB; note 2	66	_	_	dBmV
F	noise figure	see Table 1	_	_	_	dB
I _{tot}	total current consumption (DC)	note 3	_	425	435	mA

Notes

```
1. f_p = 55.25 MHz; V_p = 46 dBmV; f_q = 391.25 MHz; V_q = 46 dBmV; measured at f_p + f_q = 446.5 MHz.
```

2. Measured according to DIN45004B:

```
\begin{split} f_p &= 440.25 \text{ MHz; } V_p = V_o; \\ f_q &= 447.25 \text{ MHz; } V_q = V_o - 6 \text{ dB;} \\ f_r &= 449.25 \text{ MHz; } V_r = V_o - 6 \text{ dB;} \\ \text{measured at } f_p + f_q - f_r = 438.25 \text{ MHz.} \end{split}
```

3. The module normally operates at $V_B = 24 \text{ V}$, but is able to withstand supply transients up to 30 V.

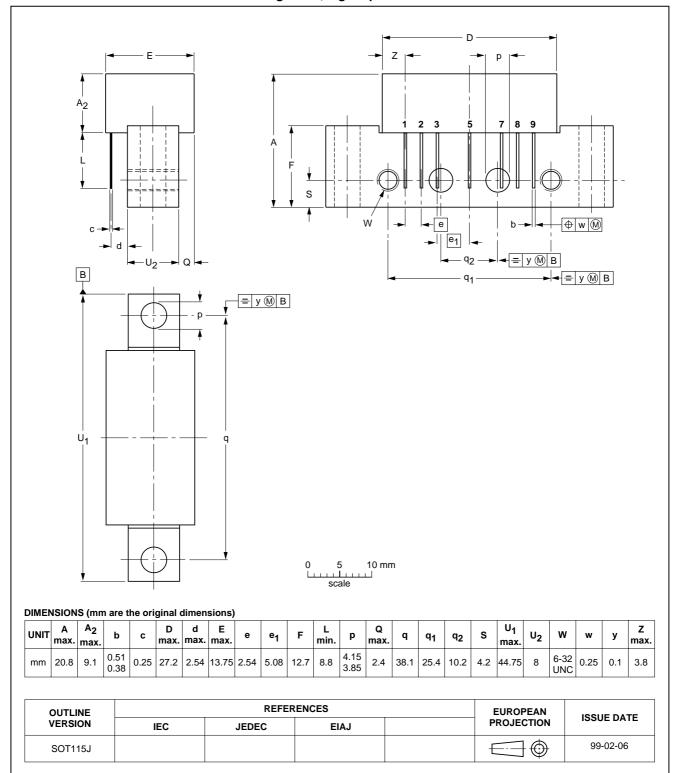
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PACKAGE OUTLINE

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J



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DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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Contact information

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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